

Supporting Information

Substantially Improved Energy Storage Capability of Ferroelectric Thin Films for Application in High-temperature Capacitors

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Supporting Information 1

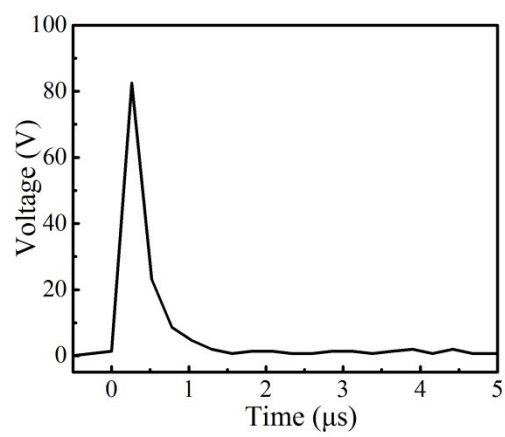


Figure S1 Charging/discharging curves of BNTZ-0.09BFO thin film.

Supporting Information 2

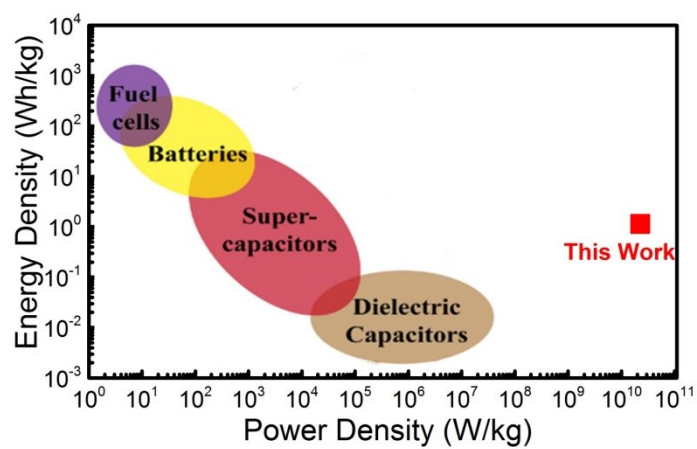


Figure S2 Comparison of energy density and power density for the BNTZ-0.09BFO thin film and other capacitors.

Supporting Information 3

Table S1 the average grain sizes BNTZ-xBFO thin films.

Samples	D (nm)	λ	θ	β
x = 0.00	30.5±0.5	0.145	16.5±0.07	0.00441±0.00002
x= 0.03	25.98±0.4	0.145	15.14±0.05	0.00518±0.00003
x = 0.06	22.1±0.3	0.145	16.37±0.04	0.00609±0.00001
x = 0.09	19.3±0. 5	0.145	16.33±0.06	0.00696±0.00001
x = 0.12	17.2±0.5	0.145	16.24±0.03	0.00781±0.00002